Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	1000
Number of Logic Elements/Cells	12800
Total RAM Bits	368640
Number of I/O	100
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	196-TFBGA, CSBGA
Supplier Device Package	196-CSPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7s15-2cpga196c

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
V_{IN}[2][3][4]	I/O input voltage.	–0.4	V_{CCO} + 0.55	V
	I/O input voltage (when V_{CCO} = 3.3V) for V_{REF} and differential I/O standards except TMDS_33.[5]	–0.4	2.625	V
V_{CCBATT}	Key memory battery backup supply.	–0.5	2.0	V
XADC				
V_{CCADC}	XADC supply relative to GNDADC.	–0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC.	–0.5	2.0	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies.[6]	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies.[6]	–	+260	°C
T_j	Maximum junction temperature.[6]	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3].
4. The maximum limit applies to DC signals. For maximum undershoot and overshoot AC specifications, see Table 4.
5. See Table 9 for TMDS_33 specifications.
6. For soldering guidelines and thermal considerations, see the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[(1)]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).	–	–	15	µA
C_{IN}[(2)]	Die input capacitance at the pad.	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	90	–	330	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	68	–	250	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	34	–	220	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	23	–	150	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	68	–	330	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state.	–	–	25	mA
I_{BATT}[(3)]	Battery supply current.	–	–	150	nA
R_{IN_TERM}[(4)]	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_40).	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_50).	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_60).	44	60	83	Ω
n	Temperature diode ideality factor.	–	1.010	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a V_{CCO}/2 level.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications from the Vivado® Design Suite as outlined in Table 12.

Table 12: **Speed Specification Version By Device**

2018.2.1	Device
1.23	XC7S6, XC7S15, XC7S25, XC7S50, XC7S75, XC7S100
1.16	XA7S6, XA7S15, XA7S25, XA7S50, XA7S75, XA7S100

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows.

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Production Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Spartan-7 FPGAs.

Table 14: **Spartan-7 Device Production Software and Speed Specification Release**

Device	V_{CCINT} Operating Voltage, Speed Grade, and Temperature Range					
	1.0V					0.95V
	-2C	-2I	-1C	-1I	-1Q	-1LI
XC7S6	Vivado tools 2018.2 v1.22				Vivado tools 2018.2.1 v1.23	Vivado tools 2018.2 v1.22
XC7S15	Vivado tools 2018.2 v1.22				Vivado tools 2018.2.1 v1.23	Vivado tools 2018.2 v1.22
XC7S25	Vivado tools 2017.4 v1.20				Vivado tools 2018.1 v1.21	Vivado tools 2017.4 v1.20
XC7S50	Vivado tools 2017.2 v1.17				Vivado tools 2017.3 v1.19	Vivado tools 2017.2 v1.17
XC7S75	Vivado tools 2018.1 v1.21				Vivado tools 2018.2.1 v1.23	Vivado tools 2018.1 v1.21
XC7S100	Vivado tools 2018.1 v1.21				Vivado tools 2018.2.1 v1.23	Vivado tools 2018.1 v1.21
XA7S6	N/A	Vivado tools 2018.2.1 v1.16	N/A	Vivado tools 2018.2.1 v1.16		N/A
XA7S15	N/A	Vivado tools 2018.2.1 v1.16	N/A	Vivado tools 2018.2.1 v1.16		N/A
XA7S25	N/A	Vivado tools 2018.1 v1.15	N/A	Vivado tools 2018.1 v1.15		N/A
XA7S50	N/A	Vivado tools 2017.3 v1.12	N/A	Vivado tools 2017.3 v1.12		N/A
XA7S75	N/A	Vivado tools 2018.2.1 v1.16	N/A	Vivado tools 2018.2.1 v1.16		N/A
XA7S100	N/A	Vivado tools 2018.2.1 v1.16	N/A	Vivado tools 2018.2.1 v1.16		N/A

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Spartan-7 FPGAs. These values are subject to the same guidelines as the AC Switching Characteristics, page 12.

Table 15: **Networking Applications Interface Performances**

Description	V_{CCINT} Operating Voltage, Speed Grade, and Temperature Range			Units
	1.0V		0.95V	
	-2C/-2I	-1C/-1I/-1Q	-1LI	
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	680	600	600	Mb/s
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 14)	1250	950	950	Mb/s
SDR LVDS receiver[1]	680	600	600	Mb/s

Table 17: **IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	V_{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVTTL_S4	1.34	1.41	1.41	3.93	4.18	4.18	3.96	4.20	4.20	ns
LVTTL_S8	1.34	1.41	1.41	3.66	3.92	3.92	3.69	3.93	3.93	ns
LVTTL_S12	1.34	1.41	1.41	3.65	3.90	3.90	3.68	3.91	3.91	ns
LVTTL_S16	1.34	1.41	1.41	3.19	3.45	3.45	3.22	3.46	3.46	ns
LVTTL_S24	1.34	1.41	1.41	3.41	3.67	3.67	3.44	3.68	3.68	ns
LVTTL_F4	1.34	1.41	1.41	3.38	3.64	3.64	3.41	3.65	3.65	ns
LVTTL_F8	1.34	1.41	1.41	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVTTL_F12	1.34	1.41	1.41	2.85	3.10	3.10	2.88	3.12	3.12	ns
LVTTL_F16	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVTTL_F24	1.34	1.41	1.41	2.65	2.90	2.90	2.68	2.91	2.91	ns
LVDS_25	0.81	0.88	0.88	1.41	1.67	1.67	1.44	1.68	1.68	ns
MINI_LVDS_25	0.81	0.88	0.88	1.40	1.65	1.65	1.43	1.66	1.66	ns
BLVDS_25	0.81	0.88	0.88	1.96	2.21	2.21	1.99	2.23	2.23	ns
RSDS_25 (point to point)	0.81	0.88	0.88	1.40	1.65	1.65	1.43	1.66	1.66	ns
PPDS_25	0.81	0.88	0.88	1.41	1.67	1.67	1.44	1.68	1.68	ns
TMDS_33	0.81	0.88	0.88	1.54	1.79	1.79	1.57	1.80	1.80	ns
PCI33_3	1.32	1.39	1.39	3.22	3.48	3.48	3.25	3.49	3.49	ns
HSUL_12_S	0.75	0.82	0.82	1.93	2.18	2.18	1.96	2.20	2.20	ns
HSUL_12_F	0.75	0.82	0.82	1.41	1.67	1.67	1.44	1.68	1.68	ns
DIFF_HSUL_12_S	0.76	0.83	0.83	1.93	2.18	2.18	1.96	2.20	2.20	ns
DIFF_HSUL_12_F	0.76	0.83	0.83	1.41	1.67	1.67	1.44	1.68	1.68	ns
MOBILE_DDR_S	0.84	0.91	0.91	1.80	2.06	2.06	1.83	2.07	2.07	ns
MOBILE_DDR_F	0.84	0.91	0.91	1.51	1.76	1.76	1.54	1.77	1.77	ns
DIFF_MOBILE_DDR_S	0.78	0.85	0.85	1.82	2.07	2.07	1.85	2.09	2.09	ns
DIFF_MOBILE_DDR_F	0.78	0.85	0.85	1.57	1.82	1.82	1.60	1.84	1.84	ns
HSTL_I_S	0.75	0.82	0.82	1.74	1.99	1.99	1.77	2.01	2.01	ns
HSTL_II_S	0.73	0.80	0.80	1.54	1.79	1.79	1.57	1.80	1.80	ns
HSTL_I_18_S	0.75	0.82	0.82	1.41	1.67	1.67	1.44	1.68	1.68	ns
HSTL_II_18_S	0.75	0.81	0.81	1.54	1.79	1.79	1.57	1.80	1.80	ns
DIFF_HSTL_I_S	0.76	0.83	0.83	1.71	1.96	1.96	1.74	1.98	1.98	ns
DIFF_HSTL_II_S	0.76	0.83	0.83	1.63	1.88	1.88	1.66	1.90	1.90	ns
DIFF_HSTL_I_18_S	0.79	0.86	0.86	1.51	1.76	1.76	1.54	1.77	1.77	ns
DIFF_HSTL_II_18_S	0.78	0.85	0.85	1.58	1.84	1.84	1.61	1.85	1.85	ns
HSTL_I_F	0.75	0.82	0.82	1.22	1.48	1.48	1.25	1.49	1.49	ns
HSTL_II_F	0.73	0.80	0.80	1.24	1.49	1.49	1.27	1.51	1.51	ns
HSTL_I_18_F	0.75	0.82	0.82	1.26	1.51	1.51	1.29	1.52	1.52	ns

Table 17: **IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	V_{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
HSTL_II_18_F	0.75	0.81	0.81	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_HSTL_I_F	0.76	0.83	0.83	1.30	1.56	1.56	1.33	1.57	1.57	ns
DIFF_HSTL_II_F	0.76	0.83	0.83	1.33	1.59	1.59	1.36	1.60	1.60	ns
DIFF_HSTL_I_18_F	0.79	0.86	0.86	1.33	1.59	1.59	1.36	1.60	1.60	ns
DIFF_HSTL_II_18_F	0.78	0.85	0.85	1.33	1.59	1.59	1.36	1.60	1.60	ns
LVCMOS33_S4	1.34	1.41	1.41	3.93	4.18	4.18	3.96	4.20	4.20	ns
LVCMOS33_S8	1.34	1.41	1.41	3.65	3.90	3.90	3.68	3.91	3.91	ns
LVCMOS33_S12	1.34	1.41	1.41	3.21	3.46	3.46	3.24	3.48	3.48	ns
LVCMOS33_S16	1.34	1.41	1.41	3.52	3.77	3.77	3.55	3.79	3.79	ns
LVCMOS33_F4	1.34	1.41	1.41	3.38	3.64	3.64	3.41	3.65	3.65	ns
LVCMOS33_F8	1.34	1.41	1.41	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVCMOS33_F12	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVCMOS33_F16	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVCMOS25_S4	1.20	1.27	1.27	3.26	3.51	3.51	3.29	3.52	3.52	ns
LVCMOS25_S8	1.20	1.27	1.27	3.01	3.26	3.26	3.04	3.27	3.27	ns
LVCMOS25_S12	1.20	1.27	1.27	2.60	2.85	2.85	2.63	2.87	2.87	ns
LVCMOS25_S16	1.20	1.27	1.27	2.94	3.20	3.20	2.97	3.21	3.21	ns
LVCMOS25_F4	1.20	1.27	1.27	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVCMOS25_F8	1.20	1.27	1.27	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS25_F12	1.20	1.27	1.27	2.29	2.54	2.54	2.32	2.55	2.55	ns
LVCMOS25_F16	1.20	1.27	1.27	2.13	2.39	2.39	2.16	2.40	2.40	ns
LVCMOS18_S4	0.83	0.89	0.89	1.74	1.99	1.99	1.77	2.01	2.01	ns
LVCMOS18_S8	0.83	0.89	0.89	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS18_S12	0.83	0.89	0.89	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS18_S16	0.83	0.89	0.89	1.65	1.90	1.90	1.68	1.91	1.91	ns
LVCMOS18_S24	0.83	0.89	0.89	1.72	1.98	1.98	1.75	1.99	1.99	ns
LVCMOS18_F4	0.83	0.89	0.89	1.57	1.82	1.82	1.60	1.84	1.84	ns
LVCMOS18_F8	0.83	0.89	0.89	1.80	2.06	2.06	1.83	2.07	2.07	ns
LVCMOS18_F12	0.83	0.89	0.89	1.80	2.06	2.06	1.83	2.07	2.07	ns
LVCMOS18_F16	0.83	0.89	0.89	1.52	1.77	1.77	1.55	1.79	1.79	ns
LVCMOS18_F24	0.83	0.89	0.89	1.46	1.71	1.71	1.49	1.73	1.73	ns
LVCMOS15_S4	0.86	0.93	0.93	2.18	2.43	2.43	2.21	2.45	2.45	ns
LVCMOS15_S8	0.86	0.93	0.93	2.21	2.46	2.46	2.24	2.48	2.48	ns
LVCMOS15_S12	0.86	0.93	0.93	1.71	1.96	1.96	1.74	1.98	1.98	ns
LVCMOS15_S16	0.86	0.93	0.93	1.71	1.96	1.96	1.74	1.98	1.98	ns
LVCMOS15_F4	0.86	0.93	0.93	1.97	2.23	2.23	2.00	2.24	2.24	ns

Table 17: **IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	V_{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVCMOS15_F8	0.86	0.93	0.93	1.72	1.98	1.98	1.75	1.99	1.99	ns
LVCMOS15_F12	0.86	0.93	0.93	1.47	1.73	1.73	1.50	1.74	1.74	ns
LVCMOS15_F16	0.86	0.93	0.93	1.46	1.71	1.71	1.49	1.73	1.73	ns
LVCMOS12_S4	0.95	1.02	1.02	2.69	2.95	2.95	2.72	2.96	2.96	ns
LVCMOS12_S8	0.95	1.02	1.02	2.21	2.46	2.46	2.24	2.48	2.48	ns
LVCMOS12_S12	0.95	1.02	1.02	1.91	2.17	2.17	1.94	2.18	2.18	ns
LVCMOS12_F4	0.95	1.02	1.02	2.10	2.35	2.35	2.13	2.37	2.37	ns
LVCMOS12_F8	0.95	1.02	1.02	1.66	1.92	1.92	1.69	1.93	1.93	ns
LVCMOS12_F12	0.95	1.02	1.02	1.51	1.76	1.76	1.54	1.77	1.77	ns
SSTL135_S	0.75	0.82	0.82	1.47	1.73	1.73	1.50	1.74	1.74	ns
SSTL15_S	0.68	0.75	0.75	1.43	1.68	1.68	1.46	1.69	1.69	ns
SSTL18_I_S	0.75	0.82	0.82	1.79	2.04	2.04	1.82	2.06	2.06	ns
SSTL18_II_S	0.75	0.82	0.82	1.43	1.68	1.68	1.46	1.70	1.70	ns
DIFF_SSTL135_S	0.76	0.83	0.83	1.47	1.73	1.73	1.50	1.74	1.74	ns
DIFF_SSTL15_S	0.76	0.83	0.83	1.43	1.68	1.68	1.46	1.69	1.69	ns
DIFF_SSTL18_I_S	0.79	0.86	0.86	1.80	2.06	2.06	1.83	2.07	2.07	ns
DIFF_SSTL18_II_S	0.79	0.86	0.86	1.51	1.76	1.76	1.54	1.77	1.77	ns
SSTL135_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
SSTL15_F	0.68	0.75	0.75	1.19	1.45	1.45	1.22	1.46	1.46	ns
SSTL18_I_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
SSTL18_II_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_SSTL135_F	0.76	0.83	0.83	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_SSTL15_F	0.76	0.83	0.83	1.19	1.45	1.45	1.22	1.46	1.46	ns
DIFF_SSTL18_I_F	0.79	0.86	0.86	1.35	1.60	1.60	1.38	1.62	1.62	ns
DIFF_SSTL18_II_F	0.79	0.86	0.86	1.33	1.59	1.59	1.36	1.60	1.60	ns

Table 18 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 19: **Input Delay Measurement Methodology *(Cont'd)***

Description	I/O Standard Attribute	V_L[1]	V_H[1]	V_{MEAS}[3][5]	V_{REF}[2][4]
PPDS_25	PPDS_25	1.25 – 0.125	1.25 + 0.125	0[5]	–
RSDS_25	RSDS_25	1.25 – 0.125	1.25 + 0.125	0[5]	–
TMDS_33	TMDS_33	3 – 0.125	3 + 0.125	0[5]	–

Notes:

1. Input waveform switches between V_L and V_H.
2. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
3. Input voltage level from which measurement starts.
4. This is an input voltage reference that bears no relation to the V_{REF} / V_{MEAS} parameters found in IBIS models and/or noted in Figure 1.
5. The value given is the differential input voltage.

Output Delay Measurements

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 1 and Figure 2.

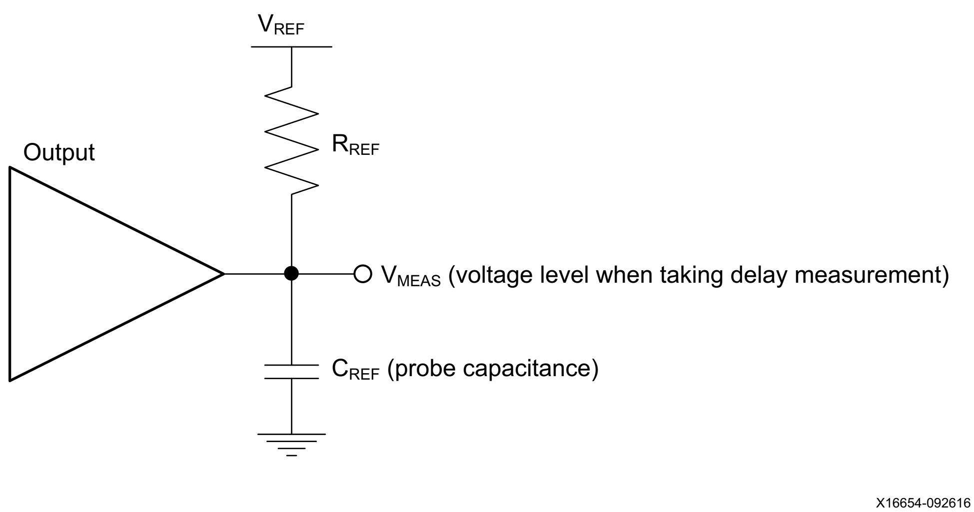

Figure 1: **Single-ended Test Setup**

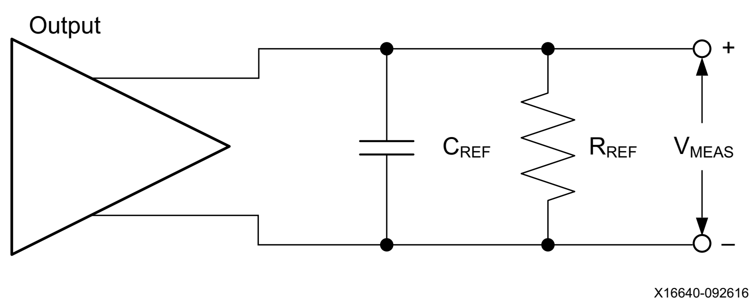

Figure 2: **Differential Test Setup**

Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from Table 20.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of step 2 and step 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Table 22: **OLOGIC Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup/Hold					
T_{ODCK}/T_{OCKD}	D1/D2 pins setup/hold with respect to CLK.	0.71/–0.11	0.84/–0.11	0.84/–0.11	ns
T_{OOCECK}/T_{OCKOCE}	OCE pin setup/hold with respect to CLK.	0.34/0.58	0.51/0.58	0.51/0.58	ns
T_{OSRCK}/T_{OCKSR}	SR pin setup/hold with respect to CLK.	0.44/0.21	0.80/0.21	0.80/0.21	ns
T_{OTCK}/T_{OCKT}	T1/T2 pins setup/hold with respect to CLK.	0.73/–0.14	0.89/–0.14	0.89/–0.14	ns
T_{OTCECK}/T_{OCKTCE}	TCE pin setup/hold with respect to CLK.	0.34/0.01	0.51/0.01	0.51/0.01	ns
Combinatorial					
T_{ODQ}	D1 to OQ out or T1 to TQ out.	0.96	1.16	1.16	ns
Sequential Delays					
T_{OCKQ}	CLK to OQ/TQ out.	0.49	0.56	0.56	ns
T_{RQ_OLOGIC}	SR pin to OQ/TQ out.	0.80	0.95	0.95	ns
T_{GSRQ_OLOGIC}	Global set/reset to Q outputs.	7.60	10.51	10.51	ns
Set/Reset					
T_{RPW_OLOGIC}	Minimum pulse width, SR inputs.	0.74	0.74	0.74	ns, Min

Input Serializer/Deserializer Switching Characteristics

Table 23: **ISERDES Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup/Hold for Control Lines					
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin setup/hold with respect to CLKDIV.	0.02/0.15	0.02/0.17	0.02/0.17	ns
T_{ISCCK_CE}/ T_{ISCKC_CE}	CE pin setup/hold with respect to CLK (for CE1).	0.50/–0.01	0.72/–0.01	0.72/–0.01	ns
T_{ISCCK_CE2}/ T_{ISCKC_CE2}	CE pin setup/hold with respect to CLKDIV (for CE2).	–0.10/0.36	–0.10/0.40	–0.10/0.40	ns
Setup/Hold for Data Lines					
T_{ISDCK_D}/ T_{ISCKD_D}	D pin setup/hold with respect to CLK.	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
T_{ISDCK_DDLY}/ T_{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY).[(1)]	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
$T_{ISDCK\_D\_DDR}$/ $T_{ISCKD\_D\_DDR}$	D pin setup/hold with respect to CLK at DDR mode.	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
$T_{ISDCK\_DDLY\_DDR}$/ $T_{ISCKD\_DDLY\_DDR}$	D pin setup/hold with respect to CLK at DDR mode (using IDELAY).[(1)]	0.14/0.14	0.17/0.17	0.17/0.17	ns
Sequential Delays					
T_{ISCKO_Q}	CLKDIV to out at Q pin.	0.54	0.66	0.66	ns
Propagation Delays					
T_{ISDO_DO}	D input to DO output pin.	0.11	0.13	0.13	ns

Notes:

1. Recorded at 0 tap value.

Output Serializer/Deserializer Switching Characteristics

Table 24: **OSERDES Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup/Hold					
T_{OSDCK_D}/ T_{OSCKD_D}	D input setup/hold with respect to CLKDIV.	0.45/0.03	0.63/0.03	0.63/0.03	ns
T_{OSDCK_T}/ T_{OSCKD_T}	T input setup/hold with respect to CLK.	0.73/–0.13	0.88/–0.13	0.88/–0.13	ns
T_{OSDCK_T2}/ T_{OSCKD_T2}	T input setup/hold with respect to CLKDIV.	0.34/–0.13	0.39/–0.13	0.39/–0.13	ns
T_{OSCCK_OCE}/ T_{OSCKC_OCE}	OCE input setup/hold with respect to CLK.	0.34/0.58	0.51/0.58	0.51/0.58	ns
T_{OSCCK_S}	SR (reset) input setup with respect to CLKDIV.	0.52	0.85	0.85	ns
T_{OSCCK_TCE}/ T_{OSCKC_TCE}	TCE input setup/hold with respect to CLK.	0.34/0.01	0.51/0.01	0.51/0.01	ns
Sequential Delays					
T_{OSCKO_OQ}	Clock to out from CLK to OQ.	0.42	0.48	0.48	ns
T_{OSCKO_TQ}	Clock to out from CLK to TQ.	0.49	0.56	0.56	ns
Combinatorial					
T_{OSDO_TTQ}	T input to TQ out.	0.92	1.11	1.11	ns

Block RAM and FIFO Switching Characteristics

Table 30: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Block RAM and FIFO Clock-to-Out Delays					
T_{RCKO_DO} and $T_{RCKO\_DO\_REG}$	Clock CLK to DOUT output (without output register).(1)(2)	2.13	2.46	2.46	ns, Max
	Clock CLK to DOUT output (with output register).(3)(4)	0.74	0.89	0.89	ns, Max
$T_{RCKO\_DO\_ECC}$ and $T_{RCKO\_DO\_ECC\_REG}$	Clock CLK to DOUT output with ECC (without output register).(1)(2)	3.04	3.84	3.84	ns, Max
	Clock CLK to DOUT output with ECC (with output register).(3)(4)	0.81	0.94	0.94	ns, Max
$T_{RCKO\_DO\_CASCOUT}$ and $T_{RCKO\_DO\_CASCOUT\_REG}$	Clock CLK to DOUT output with cascade (without output register).(1)	2.88	3.30	3.30	ns, Max
	Clock CLK to DOUT output with cascade (with output register).(3)	1.28	1.46	1.46	ns, Max
T_{RCKO_FLAGS}	Clock CLK to FIFO flags outputs.(5)	0.87	1.05	1.05	ns, Max
$T_{RCKO\_POINTERS}$	Clock CLK to FIFO pointers outputs.(6)	1.02	1.15	1.15	ns, Max
$T_{RCKO\_PARITY\_ECC}$	Clock CLK to ECCPARITY in ECC encode only mode.	0.85	0.94	0.94	ns, Max
$T_{RCKO\_SDBIT\_ECC}$ and $T_{RCKO\_SDBIT\_ECC\_REG}$	Clock CLK to BITERR (without output register).	2.81	3.55	3.55	ns, Max
	Clock CLK to BITERR (with output register).	0.76	0.89	0.89	ns, Max
$T_{RCKO\_RDADDR\_ECC}$ and $T_{RCKO\_RDADDR\_ECC\_REG}$	Clock CLK to RDADDR output with ECC (without output register).	0.88	1.07	1.07	ns, Max
	Clock CLK to RDADDR output with ECC (with output register).	0.93	1.08	1.08	ns, Max
Setup and Hold Times Before/After Clock CLK					
T_{RCCK_ADDRA}/ T_{RCKC_ADDRA}	ADDR inputs.(7)	0.49/0.33	0.57/0.36	0.57/0.36	ns, Min
$T_{RDCK\_DI\_WF\_NC}$/ $T_{RCKD\_DI\_WF\_NC}$	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode.(8)	0.65/0.63	0.74/0.67	0.74/0.67	ns, Min
$T_{RDCK\_DI\_RF}$/ $T_{RCKD\_DI\_RF}$	Data input setup/hold time when block RAM is configured in READ_FIRST mode.(8)	0.22/0.34	0.25/0.41	0.25/0.41	ns, Min
$T_{RDCK\_DI\_ECC}$/ $T_{RCKD\_DI\_ECC}$	DIN inputs with block RAM ECC in standard mode.(8)	0.55/0.46	0.63/0.50	0.63/0.50	ns, Min
$T_{RDCK\_DI\_ECCW}$/ $T_{RCKD\_DI\_ECCW}$	DIN inputs with block RAM ECC encode only.(8)	1.02/0.46	1.17/0.50	1.17/0.50	ns, Min

Table 31: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{DSPDO\_PCIN\_CARRYCASCOUT}$	PCIN input to CARRYCASCOUT output.	1.56	1.85	1.85	ns
Clock to Outs from Output Register Clock to Output Pins					
$T_{DSPCKO\_P\_PREG}$	CLK PREG to P output.	0.37	0.44	0.44	ns
$T_{DSPCKO\_CARRYCASCOUT\_PREG}$	CLK PREG to CARRYCASCOUT output.	0.59	0.69	0.69	ns
Clock to Outs from Pipeline Register Clock to Output Pins					
$T_{DSPCKO\_P\_MREG}$	CLK MREG to P output.	1.93	2.31	2.31	ns
$T_{DSPCKO\_CARRYCASCOUT\_MREG}$	CLK MREG to CARRYCASCOUT output.	2.21	2.64	2.64	ns
$T_{DSPCKO\_P\_ADREG\_MULT}$	CLK ADREG to P output using multiplier.	3.10	3.69	3.69	ns
$T_{DSPCKO\_CARRYCASCOUT\_ADREG\_MULT}$	CLK ADREG to CARRYCASCOUT output using multiplier.	3.38	4.02	4.02	ns
Clock to Outs from Input Register Clock to Output Pins					
$T_{DSPCKO\_P\_AREG\_MULT}$	CLK AREG to P output using multiplier.	4.51	5.37	5.37	ns
$T_{DSPCKO\_P\_BREG}$	CLK BREG to P output not using multiplier.	1.87	2.22	2.22	ns
$T_{DSPCKO\_P\_CREG}$	CLK CREG to P output not using multiplier.	1.93	2.30	2.30	ns
$T_{DSPCKO\_P\_DREG\_MULT}$	CLK DREG to P output using multiplier.	4.48	5.32	5.32	ns
Clock to Outs from Input Register Clock to Cascading Output Pins					
$T_{DSPCKO\_\{ACOUT;\ BCOUT\}\_\{AREG;\ BREG\}}$	CLK (ACOUT, BCOUT) to {A,B} register output.	0.73	0.87	0.87	ns
$T_{DSPCKO\_CARRYCASCOUT\_\{AREG,\ BREG\}\_MULT}$	CLK (AREG, BREG) to CARRYCASCOUT output using multiplier.	4.79	5.70	5.70	ns
$T_{DSPCKO\_CARRYCASCOUT\_BREG}$	CLK BREG to CARRYCASCOUT output not using multiplier.	2.15	2.55	2.55	ns
$T_{DSPCKO\_CARRYCASCOUT\_DREG\_MULT}$	CLK DREG to CARRYCASCOUT output using multiplier.	4.76	5.65	5.65	ns
$T_{DSPCKO\_CARRYCASCOUT\_CREG}$	CLK CREG to CARRYCASCOUT output.	2.21	2.63	2.63	ns
Maximum Frequency					
F_{MAX}	With all registers used.	550.66	464.25	464.25	MHz
F_{MAX_PATDET}	With pattern detector.	465.77	392.93	392.93	MHz
$F_{MAX\_MULT\_NOMREG}$	Two register multiply without MREG.	305.62	257.47	257.47	MHz
$F_{MAX\_MULT\_NOMREG\_PATDET}$	Two register multiply without MREG with pattern detect.	277.62	233.92	233.92	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG}$	Without ADREG.	346.26	290.44	290.44	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG\_PATDET}$	Without ADREG with pattern detect.	346.26	290.44	290.44	MHz
$F_{MAX\_NOPIPELINEREG}$	Without pipeline registers (MREG, ADREG).	227.01	190.69	190.69	MHz
$F_{MAX\_NOPIPELINEREG\_PATDET}$	Without pipeline registers (MREG, ADREG) with pattern detect.	211.15	177.43	177.43	MHz

Table 35: **Horizontal Clock Buffer Switching Characteristics (BUFH)**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{BHCKO_O}	BUFH delay from I to O.	0.11	0.13	0.13	ns
T_{BHCCK_CE}/ T_{BHCKC_CE}	CE pin setup and hold.	0.22/0.15	0.28/0.21	0.28/0.21	ns
Maximum Frequency					
F_{MAX_BUFH}	Horizontal clock buffer (BUFH).	628.00	464.00	464.00	MHz

Table 36: **Duty Cycle Distortion and Clock-Tree Skew**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
T_{DCD_CLK}	Global clock tree duty-cycle distortion.(1)	All	0.20	0.20	0.20	ns
T_{CKSKEW}	Global clock tree skew.(2)	XC7S6	0.05	0.06	0.06	ns
		XC7S15	0.05	0.06	0.06	ns
		XC7S25	0.26	0.26	0.26	ns
		XC7S50	0.26	0.26	0.26	ns
		XC7S75	0.33	0.36	0.36	ns
		XC7S100	0.33	0.36	0.36	ns
		XA7S6	0.05	0.06	N/A	ns
		XA7S15	0.05	0.06	N/A	ns
		XA7S25	0.26	0.26	N/A	ns
		XA7S50	0.26	0.26	N/A	ns
		XA7S75	0.33	0.36	N/A	ns
		XA7S100	0.33	0.36	N/A	ns
T_{DCD_BUFIO}	I/O clock tree duty cycle distortion.	All	0.14	0.14	0.14	ns
$T_{BUFIOSKEW}$	I/O clock tree skew across one clock region.	All	0.03	0.03	0.03	ns
T_{DCD_BUFR}	Regional clock tree duty cycle distortion.	All	0.18	0.18	0.18	ns

Notes:

1. These parameters represent the worst-case duty cycle distortion observable at the I/O flip flops. For all I/O standards, IBIS can be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times.
2. The T_{CKSKEW} value represents the worst-case clock-tree skew observable between sequential I/O elements. Significantly less clock-tree skew exists for I/O registers that are close to each other and fed by the same or adjacent clock-tree branches. Use the Xilinx timing analysis tools to evaluate clock skew specific to your application.

MMCM Switching Characteristics

Table 37: **MMCM Specification**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$MMCM\_F_{INMAX}$	Maximum input clock frequency.	800.00	800.00	800.00	MHz
$MMCM\_F_{INMIN}$	Minimum input clock frequency.	10.00	10.00	10.00	MHz
$MMCM\_F_{INJITTER}$	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max			
$MMCM\_F_{INDUTY}$	Allowable input duty cycle: 10—49 MHz.	25	25	25	%
	Allowable input duty cycle: 50—199 MHz.	30	30	30	%
	Allowable input duty cycle: 200—399 MHz.	35	35	35	%
	Allowable input duty cycle: 400—499 MHz.	40	40	40	%
	Allowable input duty cycle: > 500 MHz.	45	45	45	%
$MMCM\_F_{MIN\_PSCLK}$	Minimum dynamic phase-shift clock frequency.	0.01	0.01	0.01	MHz
$MMCM\_F_{MAX\_PSCLK}$	Maximum dynamic phase-shift clock frequency.	500.00	450.00	450.00	MHz
$MMCM\_F_{VCOMIN}$	Minimum MMCM VCO frequency.	600.00	600.00	600.00	MHz
$MMCM\_F_{VCOMAX}$	Maximum MMCM VCO frequency.	1440.00	1200.00	1200.00	MHz
$MMCM\_F_{BANDWIDTH}$	Low MMCM bandwidth at typical.[1]	1.00	1.00	1.00	MHz
	High MMCM bandwidth at typical.[1]	4.00	4.00	4.00	MHz
$MMCM\_T_{STATPHAOFFSET}$	Static phase offset of the MMCM outputs.[2]	0.12	0.12	0.12	ns
$MMCM\_T_{OUTJITTER}$	MMCM output jitter.	Note 3			
$MMCM\_T_{OUTDUTY}$	MMCM output clock duty-cycle precision.[4]	0.20	0.20	0.20	ns
$MMCM\_T_{LOCKMAX}$	MMCM maximum lock time.	100.00	100.00	100.00	µs
$MMCM\_F_{OUTMAX}$	MMCM maximum output frequency.	800.00	800.00	800.00	MHz
$MMCM\_F_{OUTMIN}$	MMCM minimum output frequency.[5][6]	4.69	4.69	4.69	MHz
$MMCM\_T_{EXTFDVAR}$	External clock feedback variation.	< 20% of clock input period or 1 ns Max			
$MMCM\_RST_{MINPULSE}$	Minimum reset pulse width.	5.00	5.00	5.00	ns
$MMCM\_F_{PFDMAX}$	Maximum frequency at the phase frequency detector.	500.00	450.00	450.00	MHz
$MMCM\_F_{PFDMIN}$	Minimum frequency at the phase frequency detector.	10.00	10.00	10.00	MHz
$MMCM\_T_{FBDELAY}$	Maximum delay in the feedback path.	3 ns Max or one CLKIN cycle			
MMCM Switching Characteristics Setup and Hold					
$T_{MMCMDCK\_PSEN}$/ $T_{MMCMCKD\_PSEN}$	Setup and hold of phase-shift enable.	1.04/0.00	1.04/0.00	1.04/0.00	ns

Table 45: **Clock-Capable Clock Input Setup and Hold With MMCM**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for SSTL15 Standard.[(1)(2)]						
$T_{PSMMCMCC}$/ $T_{PHMMCMCC}$	No delay clock-capable clock input and IFF[(3)] with MMCM.	XC7S6	2.73/–0.59	3.27/–0.59	3.27/–0.59	ns
		XC7S15	2.73/–0.59	3.27/–0.59	3.27/–0.59	ns
		XC7S25	2.69/–0.61	3.21/–0.61	3.21/–0.61	ns
		XC7S50	2.81/–0.62	3.35/–0.62	3.35/–0.62	ns
		XC7S75	2.81/–0.62	3.36/–0.62	3.36/–0.62	ns
		XC7S100	2.81/–0.62	3.36/–0.62	3.36/–0.62	ns
		XA7S6	2.73/–0.59	3.27/–0.59	N/A	ns
		XA7S15	2.73/–0.59	3.27/–0.59	N/A	ns
		XA7S25	2.69/–0.61	3.21/–0.61	N/A	ns
		XA7S50	2.81/–0.62	3.35/–0.62	N/A	ns
		XA7S75	2.81/–0.62	3.36/–0.62	N/A	ns
		XA7S100	2.81/–0.62	3.36/–0.62	N/A	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, lowest temperature, and highest voltage.
2. Use IBIS to determine any duty-cycle distortion incurred using various standards.
3. IFF = Input flip-flop or latch.

Table 50: **XADC Specifications *(Cont'd)***

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
Conversion Rate(4)						
Conversion time: continuous	t_{CONV}	Number of ADCCLK cycles.	26	–	32	Cycles
Conversion time: event	t_{CONV}	Number of CLK cycles.	–	–	21	Cycles
DRP clock frequency	DCLK	DRP clock frequency.	8	–	250	MHz
ADC clock frequency	ADCCLK	Derived from DCLK.	1	–	26	MHz
DCLK duty cycle			40	–	60	%
XADC Reference(5)						
External reference	V_{REFP}	Externally supplied reference voltage.	1.20	1.25	1.30	V
On-chip reference		Ground V_{REFP} pin to AGND, $-40°C \leq T_j \leq 100°C$	1.2375	1.25	1.2625	V
		Ground VREFP pin to AGND, $-55°C \leq T_j < -40°C$; $100°C < T_j \leq 125°C$	1.225	1.25	1.275	V

Notes:

1. Offset and gain errors are removed by enabling the XADC automatic gain calibration feature. The values are specified for when this feature is enabled.
2. Only specified for bitstream option XADCEnhancedLinearity = ON.
3. For a detailed description, see the *ADC* chapter in the *7 Series FPGAs and Zynq-7000 AP SoC XADC Dual 12-Bit 1 MSPS Analog-to-Digital Converter User Guide* (UG480) [Ref 9].
4. For a detailed description, see the *Timing* chapter in the *7 Series FPGAs and Zynq-7000 AP SoC XADC Dual 12-Bit 1 MSPS Analog-to-Digital Converter User Guide* (UG480) [Ref 9].
5. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted.

Revision History

The following table shows the revision history for this document:

Date	Version	Description of Revisions
07/31/2018	1.7	In Table 12, updated Vivado tools version to 2018.2.1. In Table 13, moved all speed grades for all devices to Production. In Table 14, added Vivado tools version for XC7S6, XC7S15, XC7S75, XC7S100, XA7S6, XA7S15, XA7S75, and XA7S100.
06/18/2018	1.6	In Table 12, updated Vivado tools version to 2018.2. In Table 13, moved all speed grades except -1Q (1.0V) for XC7S6 and XC7S15 to Production. In Table 14, added Vivado tools version for XC7S6 and XC7S15.
04/04/2018	1.5	Added XA7S6, XA7S15, XA7S25, XA7S75, and XA7S100 devices throughout. In Table 5, updated typical quiescent supply current values for XC7S25 and XC7S50 devices, and added values for XC7S6, XC7S15, XC7S75, and XC7S100 devices. In Table 6, updated table title and $I_{CCINTMIN}$ and $I_{CCAUXMIN}$ for XC7S75 and XC7S100 devices. In Table 13, moved all speed grades for XC7S6 and XC7S15 to Preliminary, moved -1LI (0.95V) speed grade for XC7S25 to Production, and moved all speed grades except -1Q (1.0V) for XC7S75 and XC7S100 from Preliminary to Production. In Table 14, added Vivado tools version for XC7S25, XC7S75, and XC7S100. In Table 36, Table 39, Table 40, Table 41, Table 42, Table 44, Table 45, and Table 46, changed parameter value for XA7S50 to N/A. In Table 49, added package skew values for XC7S6 and XC7S15 devices.
12/22/2017	1.4	In Table 12, updated Vivado tools version to 2017.4. In Table 13, moved all speed grades for XC7S75 and XC7S100 from Advance to Preliminary and all speed grades except -1LI (0.95V) for XC7S25 from Advance to Production. In Table 14, added Vivado tools version for XC7S25. Added Note 2 to Table 16. In Table 49, added package skew values for XC7S25 device in CSGA324 package and XC7S75 and XC7S100 devices in FGGA676 package.
11/20/2017	1.3	Added XA7S50 device throughout. Updated description of offered temperature ranges in second paragraph of Introduction. Added row for junction temperature (T_j) at expanded (Q) temperature to Table 2. Added -1Q (1.0V) speed grade to Table 5, and Table 13 to Table 16. In Table 12, updated Vivado tools version to 2017.3. In Table 49, added package skew values for XC7S25, XC7S50, XC7S75, and XC7S100 devices in CSGA225, FTGB196, and FGGA484 packages. Added *XA Spartan-7 Automotive FPGA Data Sheet: Overview* (DS171) to References.
06/20/2017	1.2	Updated paragraph before Table 6. In Table 12, updated Vivado tools version to 2017.2. In Table 13, moved all speed grades for XC7S50 from Preliminary to Production and updated Note 1. In Table 14, added Vivado tools version for XC7S50. In Table 49, added package skew value for XC7S50 device in FGGA484 package.
04/07/2017	1.1	Added 1.35V to Note 5 in Table 2. In Table 12, updated Vivado tools version to 2016.4. In Table 13, moved all speed grades for XC7S50 from Advance to Preliminary. Removed SFI-4.1 and SPI-4.2 from descriptions of SDR LVDS receiver and DDR LVDS receiver, respectively, in Table 15. In Table 25, changed $T_{IDELAYRESOLUTION}$ units from ps to µs. Removed BUFMR from Note 1 in Table 34. In Table 49, replaced TQGA144 with FTGB196 for XC7S6, XC7S15, and XC7S25 devices, added FTGB196 package for XC7S50 device, and added package skew value for XC7S50 device in CSGA324 package.
09/27/2016	1.0	Initial Xilinx release.

Please Read: Important Legal Notices

Automotive Applications Disclaimer

AUTOMOTIVE PRODUCTS (IDENTIFIED AS "XA" IN THE PART NUMBER) ARE NOT WARRANTED FOR USE IN THE DEPLOYMENT OF AIRBAGS OR FOR USE IN APPLICATIONS THAT AFFECT CONTROL OF A VEHICLE ("SAFETY APPLICATION") UNLESS THERE IS A SAFETY CONCEPT OR REDUNDANCY FEATURE CONSISTENT WITH THE ISO 26262 AUTOMOTIVE SAFETY STANDARD ("SAFETY DESIGN"). CUSTOMER SHALL, PRIOR TO USING OR DISTRIBUTING ANY SYSTEMS THAT INCORPORATE PRODUCTS, THOROUGHLY TEST SUCH SYSTEMS FOR SAFETY PURPOSES. USE OF PRODUCTS IN A SAFETY APPLICATION WITHOUT A SAFETY DESIGN IS FULLY AT THE RISK OF CUSTOMER, SUBJECT ONLY TO APPLICABLE LAWS AND REGULATIONS GOVERNING LIMITATIONS ON PRODUCT LIABILITY.